

ABSTRACT

The object of the present invention is to provide a method for enabling the production of endohedral fullerenes at an improved yield, and a device therefor.

Provided is a device comprising an evacuated vessel 1, means 3, 4 for forming a plasma flow 2 of an atom to be doped, means 8 for introducing fullerenes into the plasma flow 2, means 6 for holding a deposition plate consisting of a plurality of concentric separate plate components 5a, 5b, 5c which is set so as to be downstream of the plasma flow 2, and means 7a, 7b, 7c for applying bias voltages appropriately chosen independently of each other to the respective plate components 5a, 5b, 5c.